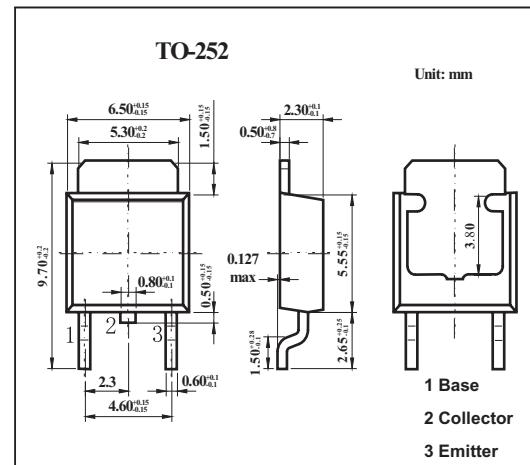


NPN Silicon Triple Diffused Transistor

2SC3405

■ Features

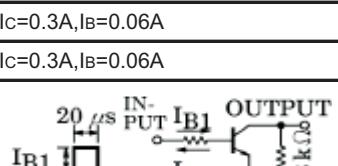
- Excellent Switching Times
 $t_r=1.0\mu s$ (Max.) $t_f=1.0\mu s$ (Max.) at $I_c=0.3A$
 - High collector Breakdown Voltage: $V_{CEO}=800V$



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector to base voltage	V _{CBO}	900	V
Collector to emitter voltage	V _{CEO}	800	V
Emitter to base voltage	V _{EBO}	8	V
Collector current (DC)	I _C	0.8	A
Collector current (Pulse)	I _{CP}	1.5	A
Base Current	I _B	0.2	A
Total Power dissipation Ta = 25°C Tc = 25°C	P _C	1 20	W W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
collector cutoff current	I _{CBO}	V _{CB} =800V,I _E =0			100	µA
emitter cutoff current	I _{EBO}	V _{EB} =8V,I _C =0			1	mA
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E =1mA,I _C =0	900			V
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =10mA,I _B =0	800			V
DC current Gain	h _{FE}	V _{CE} =5V,I _C =1mA	6			
		V _{CE} =5V,I _C =0.3A	10			
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =0.3A,I _B =0.06A			0.5	V
Base- Emitter Saturation Voltage	V _{BE(sat)}	I _C =0.3A,I _B =0.06A			1.2	V
Switching time turn-on time	tr	 $I_{B1} = -I_{B2} = 0.06 \text{ A}$, DUTY CYCLE $\leq 1\%$			1	µs
Switching storage time	tstg				4.0	µs
Switching fall time	tf				1	µs